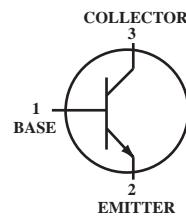


General Purpose NPN Silicon Transistor

Pb Lead(Pb)-Free



**SC-89
SOT-523F**

Maximum Ratings

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V _{CEO}	40	Vdc
Collector-Base Voltage	V _{CBO}	60	Vdc
Emitter-Base Voltage	V _{EBO}	6.0	Vdc
Collector Current-Continuous	I _C	200	mA

Thermal Characteristics

Characteristics	Symbol	Max	Unit
Total Device Dissipation FR-5 Board ⁽¹⁾ TA=25°C Derate above 25°C	P _D	200 1.6	mW mW/°C
Thermal Resistance, Junction to Ambient	R _{θJA}	600	°C/W
Total Device Dissipation Alumina Substrate, ⁽²⁾ TA=25°C Derate above 25°C	P _D	300 2.4	mW mW/°C
Thermal Resistance, Junction to Ambient	R _{θJA}	400	°C/W
Junction Temperature	T _J	-55 to +150	°C
Storage Temperature	T _{stg}	-55 to +150	°C

Device Marking

MMBT3904T=AM

Electrical Characteristics (TA=25°C Unless Otherwise noted)

Characteristics	Symbol	Min	Max	Unit
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Off Characteristics

Collector-Emitter Breakdown Voltage ⁽³⁾ (I _C =1.0mA, I _B =0)	V _{(BR)CEO}	40	-	V
Collector-Base Breakdown Voltage (I _C =10 μA, I _E =0)	V _{(BR)CBO}	60	-	V
Emitter-Base Breakdown Voltage (I _E =10 μA, I _C =0)	V _{(BR)EBO}	6.0	-	V
Base Cutoff Current (V _{CE} =30 V, V _{EB} =3.0 V)	I _{BL}	-	50	nA
Collector Cutoff Current (V _{CE} =30V, V _{EB} =3.0V)	I _{CEX}	-	50	nA

1. FR-4 Minimum Pad.

2. FR-4 1.0 x 1.0 Inch Pad.

3. Pulse Test : Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

Electrical Characteristics ($T_A=25^\circ C$ unless otherwise noted) (Continued)

Characteristics	Symbol	Min	Max	Unit
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On Characteristics⁽³⁾

DC Current Gain ($I_C= 0.1 \text{ mA}, V_{CE}=1.0\text{V}$) ($I_C= 1.0 \text{ mA}, V_{CE}= 1.0 \text{ V}$) ($I_C= 10 \text{ mA}, V_{CE}= 1.0\text{V}$) ($I_C= 50 \text{ mA}, V_{CE}= 1.0\text{V}$) ($I_C= 100 \text{ mA}, V_{CE}= 1.0\text{V}$)	H_{FE}	40 70 100 60 30	- - 300 - -	-
Collector-Emitter Saturation Voltage ⁽³⁾ ($I_C= 10 \text{ mA}, I_B= 1.0\text{mA}$) ($I_C= 50 \text{ mA}, I_B= 5.0\text{mA}$)	$V_{CE(\text{sat})}$	- -	0.2 0.3	V
Base-Emitter Saturation Voltage ⁽³⁾ ($I_C= 10 \text{ mA}, I_B= 1.0 \text{ mA}$) ($I_C= 50 \text{ mA}, I_B= 5.0 \text{ mA}$)	$V_{BE(\text{sat})}$	0.65 -	0.85 0.95	V

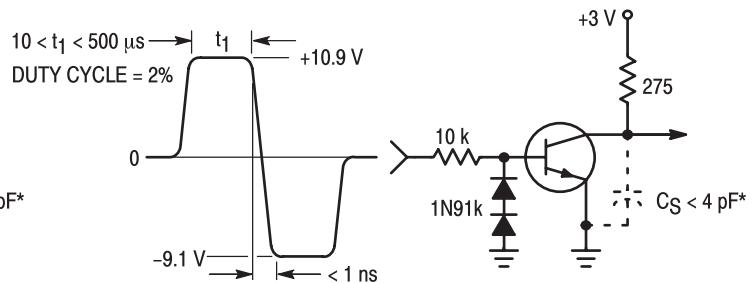
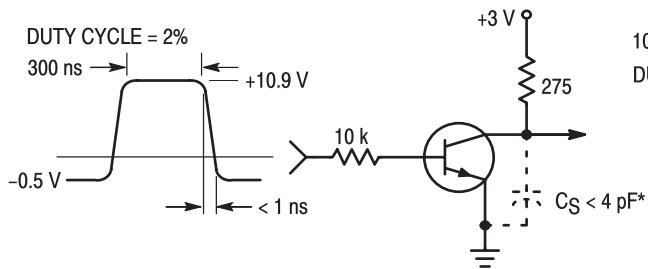
Small-signal Characteristics

Current-Gain-Bandwidth Product ($I_C= 10 \text{ mA}, V_{CE}= 20 \text{ V}, f=100\text{MHz}$)	f_T	200	-	MHz
Output Capacitance ($V_{CB}= 5.0 \text{ V}, I_E=0, f=1.0\text{MHz}$)	$C_{o\text{bo}}$	-	4.0	pF
Input Capacitance ($V_{EB}= 0.5 \text{ V}, I_C=0, f=1.0\text{MHz}$)	$C_{i\text{bo}}$	-	8.0	pF
Input Impedance ($V_{CE}= 10 \text{ V}, I_C=1.0 \text{ mA}, f=1.0 \text{ kHz}$)	h_{ie}	1.0	10	k Ω
Voltage Feedback Ratio ($V_{CE}= 10 \text{ V}, I_C=1.0 \text{ mA}, f=1.0 \text{ kHz}$)	h_{re}	0.5	8.0	$\times 10^{-4}$
Small-Signal Current Gain ($V_{CE}= 10 \text{ V}, I_C=1.0 \text{ mA}, f=1.0 \text{ kHz}$)	h_{fe}	100	400	-
Output Admittance ($V_{CE}= 10 \text{ V}, I_C=1.0 \text{ mA}, f=1.0\text{kHz}$)	h_{oe}	1.0	40	umhos
Noise Figure ($V_{CE}= 5.0 \text{ V}, I_C= 100 \mu\text{A}, R_S=1.0\text{k}\Omega, f=1.0\text{kHz}$)	NF	-	5.0	dB

Switching Characteristics

Delay Time	$(V_{CC}= 3.0 \text{ V}, V_{BE}= 0.5\text{V}$ $I_C= 10 \text{ mA}, I_{B1}= 1.0 \text{ mA})$	t_d	-	35	ns
Rise Time		t_r	-	35	
Storage Time	$(V_{CC}= 3.0 \text{ V},$ $I_C= 10 \text{ mA}, I_{B1}=I_{B2}= 1.0 \text{ mA})$	t_s	-	200	ns
Fall Time		t_f	-	50	

3. Pulse Test : Pulse Width $\leq 300 \mu\text{s}$, Duty Cycle $\leq 2.0\%$.



* Total shunt capacitance of test jig and connectors

**Figure 1. Delay and Rise Time
Equivalent Test Circuit**

**Figure 2. Storage and Fall Time
Equivalent Test Circuit**

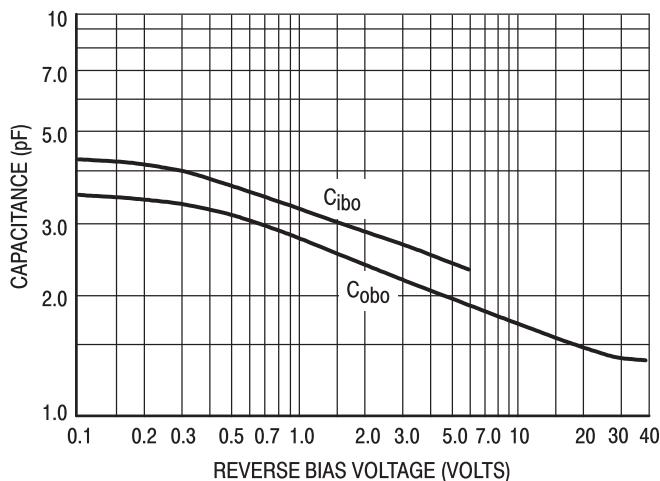


Figure 3. Capacitance

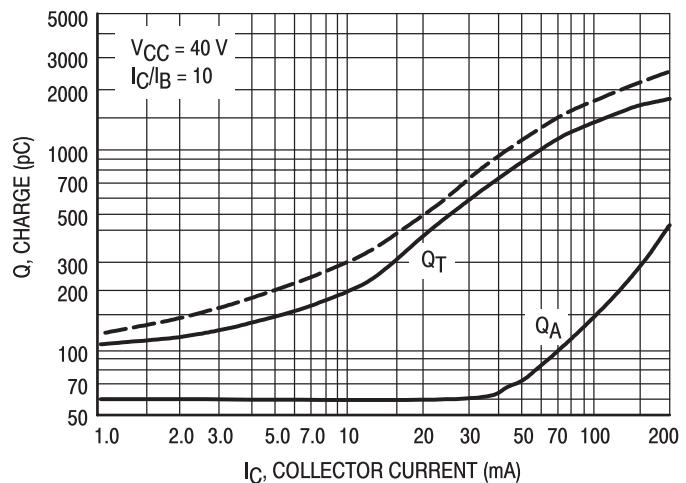
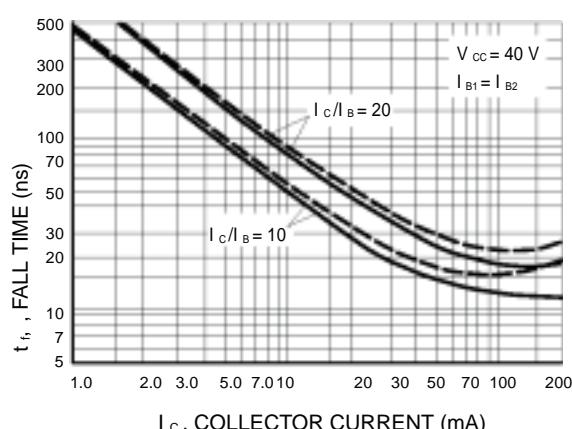
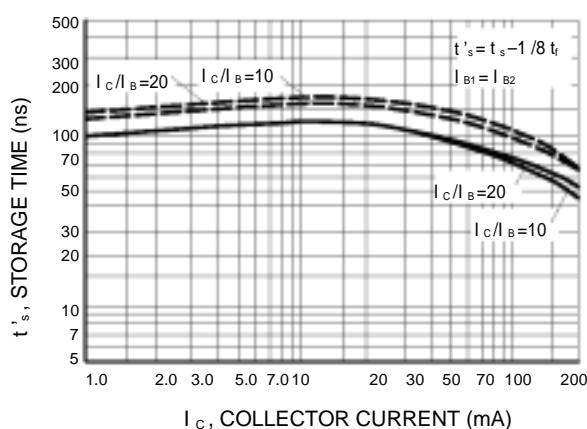
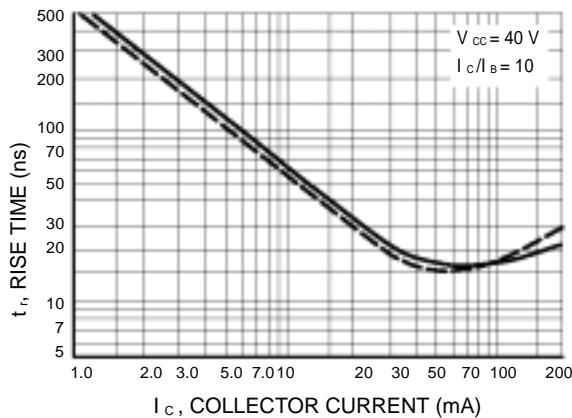
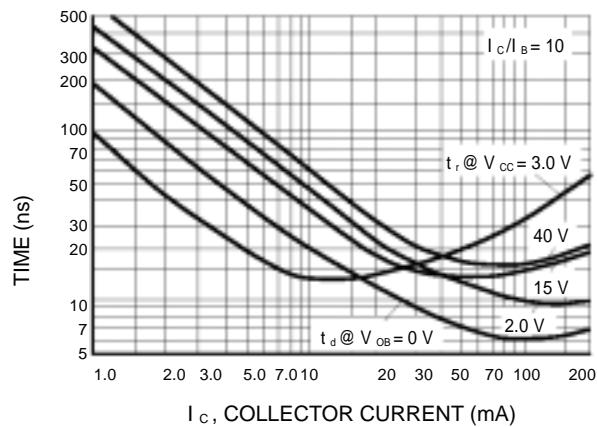
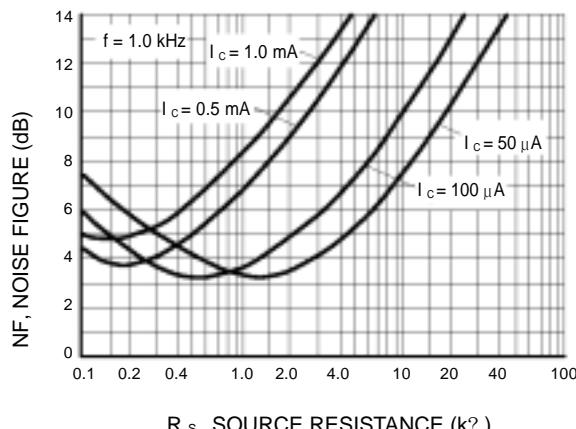
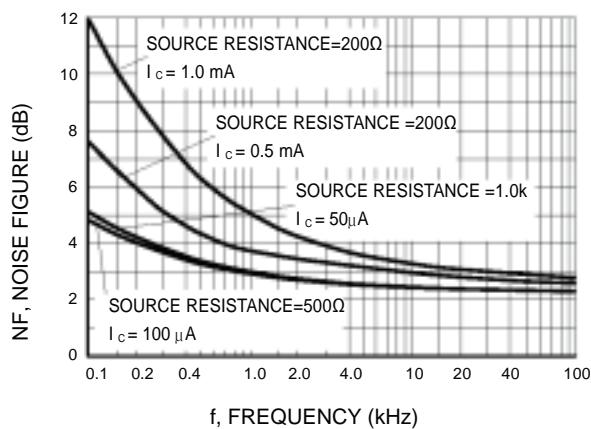


Figure 4. Charge Data



TYPICAL AUDIO SMALL-SIGNAL CHARACTERISTICS NOISE FIGURE VARIATIONS

($V_{CE} = 5.0$ V, $T_A = 25^\circ\text{C}$, Bandwidth = 1.0 Hz)



h PARAMETERS

($V_{CE} = 10$ Vdc, $f = 1.0$ kHz, $T_A = 25^\circ\text{C}$)

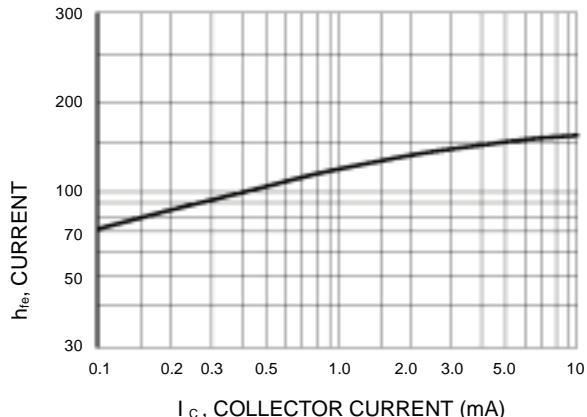


Figure 11. Current Gain

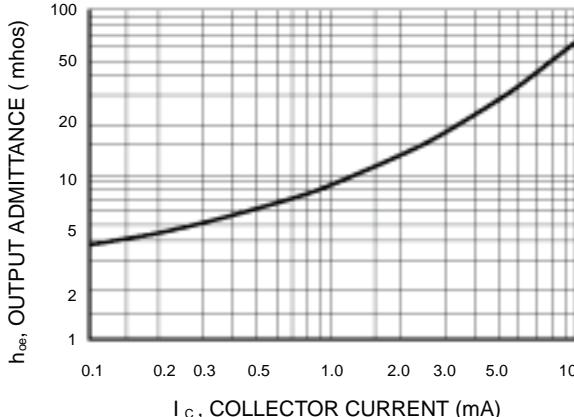


Figure 12. Output Admittance

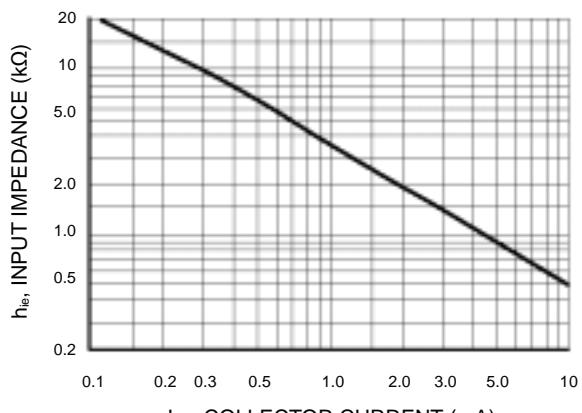


Figure 13. Input Impedance

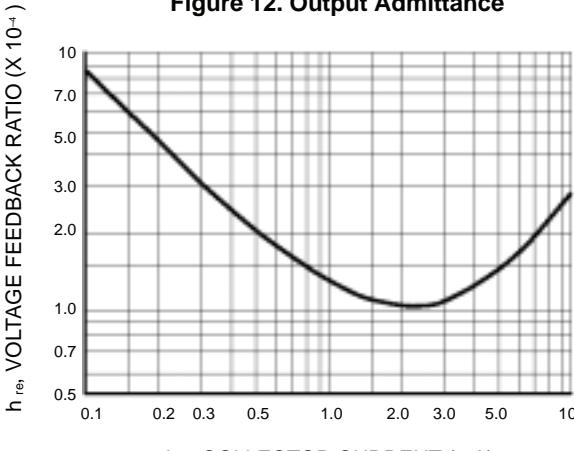


Figure 14. Voltage Feedback Ratio

TYPICAL STATIC CHARACTERISTICS

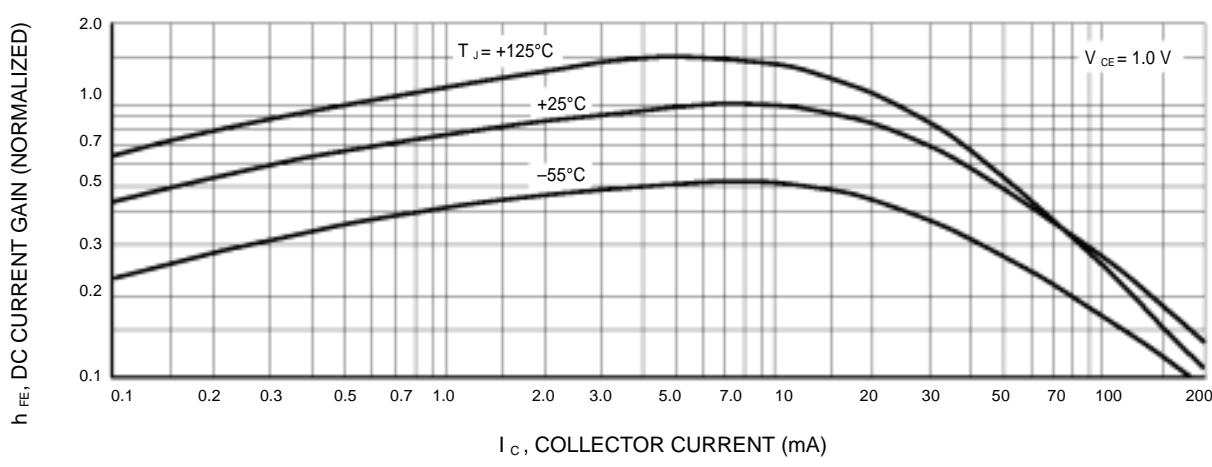


Figure 15. DC Current Gain

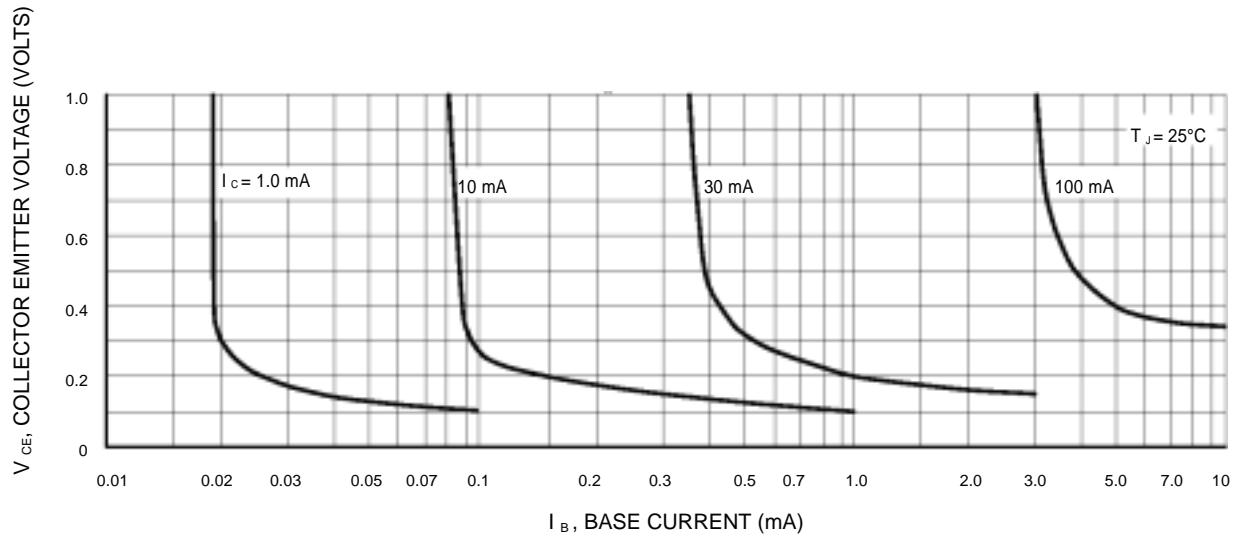
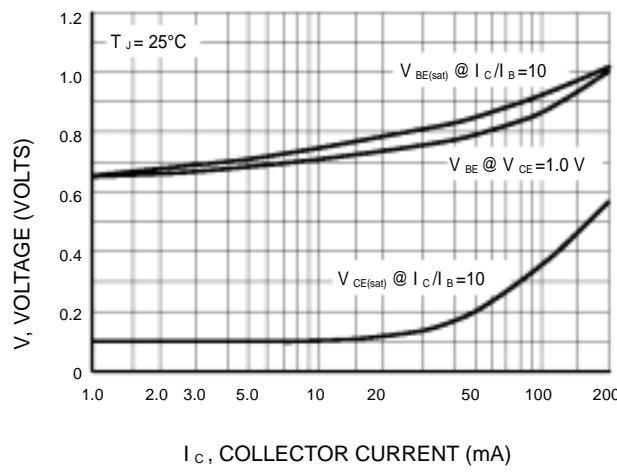
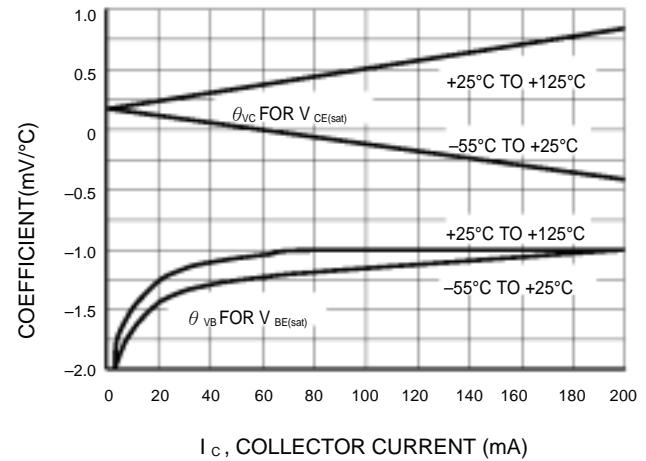


Figure 16. Collector Saturation Region



I_C , COLLECTOR CURRENT (mA)

Figure 17. "ON" Voltages

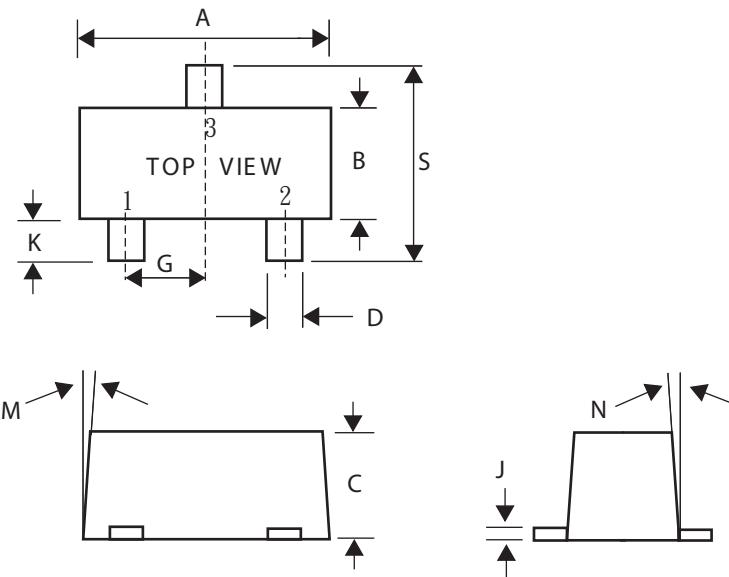


I_C , COLLECTOR CURRENT (mA)

Figure 18. Temperature Coefficients

SC-89 Package Outline Dimensions

Unit:mm



SC-89			
Dim	Min	Nom	Max
A	1.50	1.60	1.70
B	0.75	0.85	0.95
C	0.60	0.70	0.80
D	0.23	0.28	0.33
G	0.50BSC		
J	0.10	0.15	0.20
K	0.30	0.40	0.50
M	---	---	10°
N	---	---	10°
S	1.50	1.60	1.70